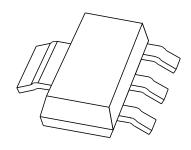
DISCRETE SEMICONDUCTORS

DATA SHEET



PBYR2100CT series Schottky barrier double diodes

Product specification Supersedes data of 1996 May 03 File under Discrete Semiconductors, SC01 1996 Oct 14





Schottky barrier double diodes

PBYR2100CT series

FEATURES

- · Low switching losses
- High breakdown voltage
- · Fast recovery time
- · Guard ring protected
- Plastic SMD package.

APPLICATIONS

- Low power, switched-mode power supplies
- Rectification
- · Polarity protection.

DESCRIPTION

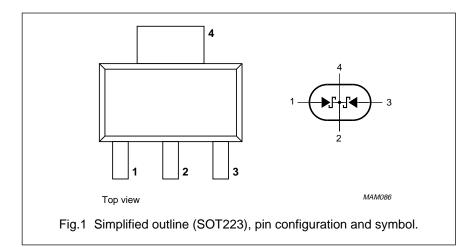
The PBYR2100CT series consists of Schottky barrier double diodes, fabricated in planar technology, and encapsulated in SOT223 plastic SMD packages.

PINNING

PIN	DESCRIPTION	
1	anode (a ₁)	
2	common cathode	
3	anode (a ₂)	
4	common cathode	

MARKING

TYPE NUMBER	MARKING CODE
PBYR280CT	BYR28
PBYR290CT	BYR29
PBYR2100CT	BYR210



Schottky barrier double diodes

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode			•	-	•
V _R	continuous reverse voltage PBYR280CT		_	80	V
	PBYR290CT		_	90	V
	PBYR2100CT		_	100	V
V _{RRM}	repetitive peak reverse voltage				
	PBYR280CT		_	80	V
	PBYR290CT		_	90	V
	PBYR2100CT		_	100	V
V _{RWM}	crest working reverse voltage				
	PBYR280CT		_	80	V
	PBYR290CT		_	90	V
	PBYR2100CT		_	100	V
I _{F(AV)}	average forward current	T_{amb} = 85 °C; see Fig.2; $R_{th j-a}$ = 70 K/W; note 1; $V_{R(equiv)}$ = 0.2 V; note 2	_	1	A
I _{FSM}	non-repetitive peak forward current	t = 8.3 ms half sine wave; JEDEC method	_	10	A
I _{RSM}	non-repetitive peak reverse current	t _p = 100 μs	_	0.5	А
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-65	+150	°C
T _{amb}	operating ambient temperature		_	85	°C

Notes

- 1. Refer to SOT223 standard mounting conditions.
- 2. For Schottky barrier diodes thermal run-away has to be considered, as in some applications, the reverse power losses P_R are a significant part of the total power losses. Nomograms for determination of the reverse power losses P_R and $I_{F(AV)}$ rating will be available on request.

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ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per diode						
V _F	forward voltage	see Fig.3				
		I _F = 1 A; note 1	_	_	790	mV
		I _F = 1 A; T _j = 100 °C; note 1	_	_	690	mV
I _R	reverse current	V _R = V _{RRMmax} ; note 1; see Fig.4	_	_	0.5	mA
		V _R = V _{RRMmax} ; T _j = 100 °C; note 1; see Fig.4	_	_	5	mA
C _d	diode capacitance	V _R = 4 V; f = 1 MHz; see Fig.5	_	_	100	pF

Note

1. Pulsed test: $t_p = 300 \ \mu s; \ \delta = 0.02$.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	70	K/W

Note

1. Refer to SOT223 standard mounting conditions.

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GRAPHICAL DATA

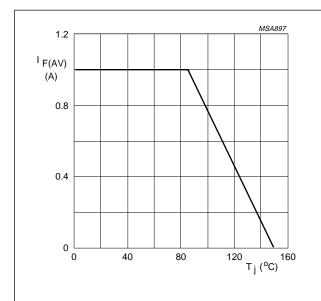
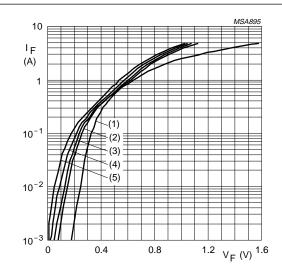
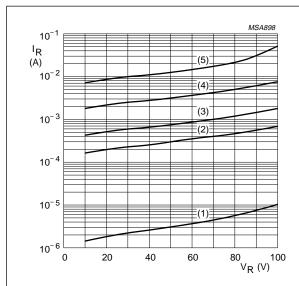


Fig.2 Average forward current derating curve.



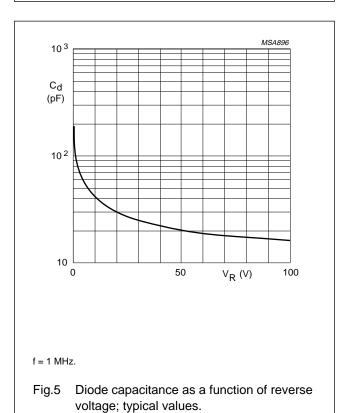
- (1) $T_{amb} = 25 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 100 \,^{\circ}C$.
- (4) $T_{amb} = 125 \,^{\circ}C$.
- (5) $T_{amb} = 150 \,^{\circ}C$.

Fig.3 Forward current as a function of forward voltage; typical values.



- (1) $T_{amb} = 25 \,^{\circ}C$.
- (2) $T_{amb} = 85 \,^{\circ}C$.
- (3) $T_{amb} = 100 \, ^{\circ}C$.
- (4) $T_{amb} = 125 \,^{\circ}C$.
- (5) $T_{amb} = 150 \,^{\circ}C$.

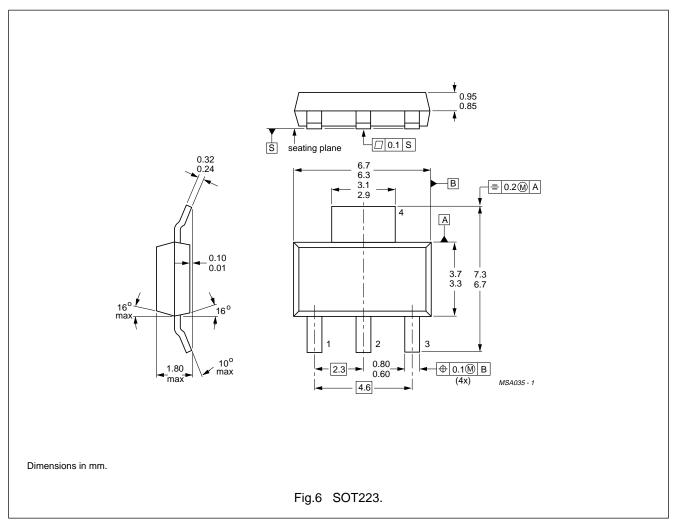
Fig.4 Reverse current as a function of reverse voltage; typical values.



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PACKAGE OUTLINE



Schottky barrier double diodes

PBYR2100CT series

DEFINITIONS

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	This data sheet contains final product specifications.			
Limiting values				
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.				

LIFE SUPPORT APPLICATIONS

Application information

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

Where application information is given, it is advisory and does not form part of the specification.